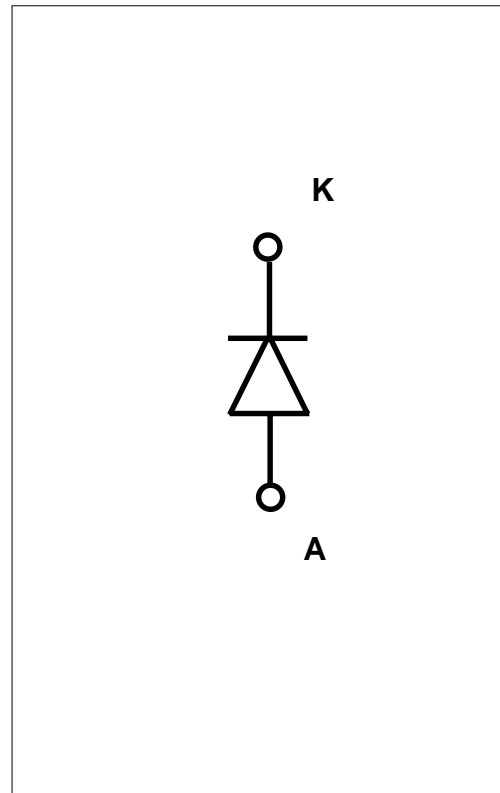
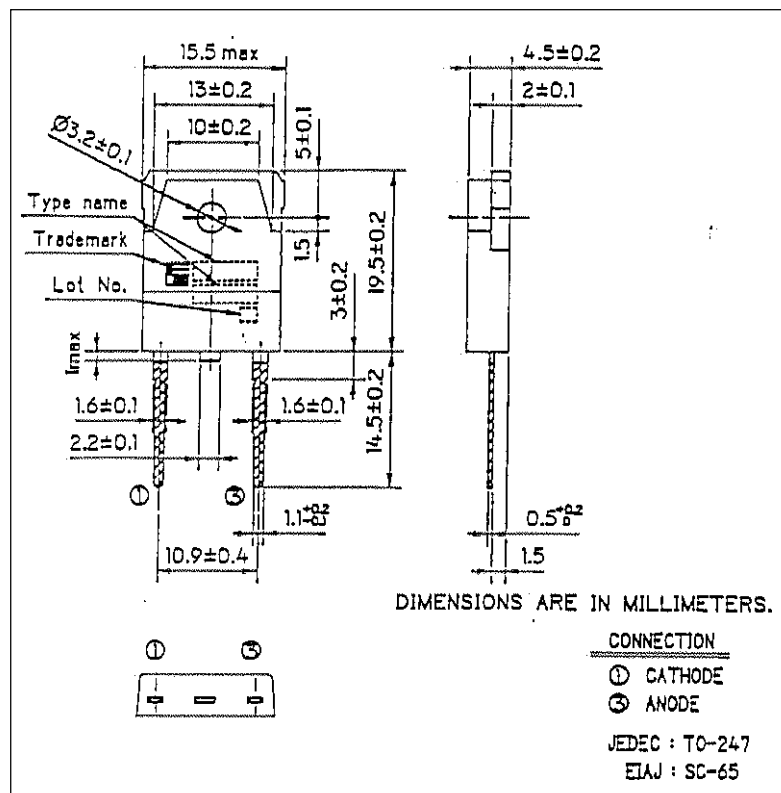


Fast Recovery Diode for IGBT

Outline Drawings Units mm

Equivalent circuit



Maximum ratings and characteristics

Absolute maximum ratings (Tc=25°C)

Item	Symbol	Test Conditions	Ratings	Units	
Repetitive Reverse Voltage	V _{RRM}		1200	V	
Repetitive peak surge current	I _{FM}	20kHz Duty 50% Squ. wave	T _c =113°C	25	A
			T _c =25°C	63	A
Average rectified forward current	I _{F(A)}	DC	25	A	
Non-repetitive peak surge current	I _{FSM}	Pulse 10ms, sin. wave	120	A	
Maximum Power Dissipation	P _o		110	W	
Operating Temperature	T _j		+150	°C	
Storage Temperature	T _{stg}		-40 to +150	°C	
Mounting Screw Torque			50	N-cm	

Electrical characteristics (at Tc=25°C unless otherwise specified)

Item	Symbol	Test Conditions	Max	Units
Reverse Current	I _R	V _R = 1200V	1.0	mA
Forward voltage	V _{FM}	I _F = 25A	3.0	V
Reverse recovery time	t _{rr}	I _F = 25A, V _R =200V, di/dt=100A/μs	0.3	μs

Thermal resistance characteristics

Item	Symbol	Test Conditions	Max	Units
Thermal resistance	R _{th(j-c)}	junction to case	1.13	°C/W

Characteristics

